Listing of Claims

This listing of claims replaces all prior versions, and listings, of claims in the application:

Claims 1-11.   (Canceled)

12.   (Currently Amended)   A phase shift mask comprising:

a plurality of regions having different step heights;

a first continuous sloped phase edge between first adjacent regions having different step heights, [[,]] wherein the first continuous sloped phase edge spans a first lateral distance between the first adjacent regions; and

a second continuous sloped phase edge between second adjacent regions having different step heights, wherein the second continuous sloped phase edge spans a second lateral distance between the second adjacent regions.

13. (Previously Presented) The phase shift mask of claim 12, wherein:

the phase shift mask is adapted to expose a substrate using electromagnetic radiation having a wavelength; and

the first lateral distance is on the order of said wavelength.

14. (Previously Presented) The phase shift mask of claim 12, wherein the phase shift mask further comprises:

a third continuous sloped phase edge between third adjacent regions having different step heights, wherein the third continuous sloped phase edge spans a third lateral distance between the third adjacent regions.

15. (Previously Presented) The phase shift mask of claim 12, wherein the first continuous sloped phase edge is perpendicular to the second continuous sloped phase edge.

16. (Previously Presented) The phase shift mask of claim 12, wherein the phase shift mask comprises a transmission phase shift mask.

17. (Previously Presented) A method comprising:

exposing a substrate using a phase shift mask that comprises a pattern comprising a plurality of regions having different step heights, a first continuous sloped phase edge between first adjacent regions having different step heights, and a second continuous sloped phase edge between second adjacent regions having different step heights to image the pattern onto a layer of resist material on the substrate,

wherein the first continuous sloped phase edge spans a first lateral distance between the first adjacent regions and the second continuous sloped phase edge spans a second lateral distance between the second adjacent regions.

18. (Original) The method of claim 17, further comprising:

developing the resist material without a second exposure.

19. (Original) The method of claim 18, wherein the second exposure comprises a trim mask exposure.

20. (Previously Presented) The method of claim 17, wherein:

said exposing comprises exposing the substrate using electromagnetic radiation having a wavelength ; and

the first lateral distance is on the order of the wavelength.

21. (Previously Presented) The method of claim 17, wherein:

the regions having different step heights comprise clear phase shift regions.

22. (Canceled)

23. (Previously Presented) The phase shift mask of claim 12, wherein the plurality of regions comprises a plurality of clear regions.

24. (Previously Presented) The phase shift mask of claim 12, wherein the first adjacent regions having different step heights comprise adjacent 0 and π regions.

25. (Previously Presented) The phase shift mask of claim 12, wherein:

the first lateral distance is dimensioned to avoid phase conflict between the first adjacent regions; and

the second lateral distance is dimensioned to avoid phase conflict between the second adjacent regions.

26. (Previously Presented) The method of claim 17, wherein the first adjacent regions having different step heights comprise adjacent 0 and π regions.

27. (Previously Presented) The method of claim 17, wherein exposing the substrate using the phase shift mask comprises shifting a phase of light transmitted through the phase shift mask.

28. (Previously Presented) The method of claim 17, wherein:

the first lateral distance is dimensioned to avoid phase conflict between the first adjacent regions; and

the second lateral distance is dimensioned to avoid phase conflict between the second adjacent regions.

29. (New) The phase shift mask of claim 12, wherein the first lateral distance differs from the second lateral distance.

30. (New) The method of claim 17, wherein the first lateral distance differs from the second lateral distance.